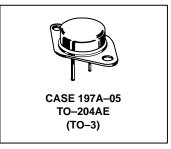
SWITCHMODE Series NPN Silicon Power Transistor

- ... designed for high current, high speed, high power applications.
- High DC current gain: HFE min. = 15 at IC = 8 A
- Low VCE(sat), VCE(sat) max. = 0.8 V at IC = 8 A
 Very fast switching times:
- $T_F = 0.4 \,\mu s$ at $I_C = 16 \,A$

BUV23

30 AMPERES **NPN SILICON POWER METAL TRANSISTOR 325 VOLTS 250 WATTS**



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO(sus)	325	Vdc
Collector–Base Voltage	V _{CBO}	400	Vdc
Emitter–Base Voltage	V _{EBO}	7	Vdc
Collector–Emitter Voltage (V _{BE} = −1.5 V)	VCEX	400	Vdc
Collector–Emitter Voltage (R _{BE} = 100 Ω)	VCER	390	Vdc
Collector–Current— Continuous — Peak (pw ≤ 10 ms)	IC ICM	30 40	Adc Apk
Base–Current continuous	IB	6	Adc
Total Power Dissipation @ T _C = 25°C	PD	250	Watts
Operating and Storage JunctionTemperature Range	T _J ,T _{stg}	-65 to 200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θЈС	0.7	°C/W

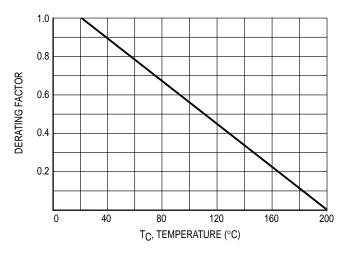


Figure 1. Power Derating

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ELECTRICAL CHARACTERISTICS (T $_{C}$ = 25 $^{\circ}$ C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit	
OFF CHARACTERISTICS ¹						
Collector–Emitter Sustaining Voltage (I _C = 200 mA, I _B = 0, L = 25 mH)		VCEO(sus)	325		Vdc	
Collector Cutoff Current at Reverse Bias $(V_{CE} = 400 \text{ V}, V_{BE} = -1.5 \text{ V})$ $(V_{CE} = 400 \text{ V}, V_{BE} = -1.5 \text{ V}, T_{C} = 125^{\circ}\text{C})$		ICEX		3.0 12	mAdc	
Collector–Emitter Cutoff Current (V _{CE} = 260 V)	ICEO		3.0	mAdc		
Emitter–Base Reverse Voltage (I _E = 50 mA)	V _{EBO}	7		V		
Emitter–Cutoff Current (V _{EB} = 5 V)	I _{EBO}		1.0	mAdc		
SECOND BREAKDOWN						
Second Breakdown Collector Cu (V _{CE} = 20 V, t = 1 s) (V _{CE} = 140 V, t = 1 s)	I _{S/b}	12 0.15		Adc		
ON CHARACTERISTICS ¹				•	•	
DC Current Gain (I _C = 8 A, V _{CE} = 4 V) (I _C = 16 A, V _{CE} = 4 V)		hFE	15 8	60		
Collector–Emitter Saturation Volt (I _C = 8 A, I _B = 1.6 A) (I _C = 16 A, I _B = 3.2 A)	age	VCE(sat)		0.8 1.0	Vdc	
Base–Emitter Saturation Voltage (I _C = 16 A, I _B = 3.2 A)		V _{BE} (sat)		1.5	Vdc	
DYNAMIC CHARACTERISTICS						
Current Gain — Bandwidth Product (V _{CE} = 15 V, I _C = 2 A, f = 4 MHz)		fT	8.0		MHz	
SWITCHING CHARACTERISTICS	S (Resistive Load)			•	•	
Turn-on Time		ton		0.8	μs	
Storage Time	$(I_C = 16 \text{ A}, I_{B1} = I_{B2} = 3.2 \text{ A}, V_{CC} = 100 \text{ V}, R_C = 6.25 \Omega)$	t _S		2.5		
Fall Time	· () = 100 v, (v) = 0.20 22)	t _f		0.4	7	

¹Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2\%$.

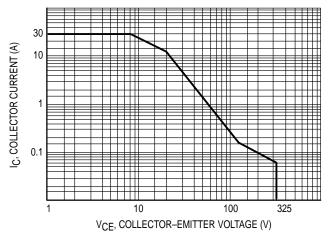


Figure 2. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_{\text{C}} - V_{\text{CE}}$ limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_C = 25^{\circ}C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown limitations do not derate the same as thermal limitations.

At high case temperatures, thermal limitations will reduce the power that can handled to values less than the limitations imposed by second breakdown.

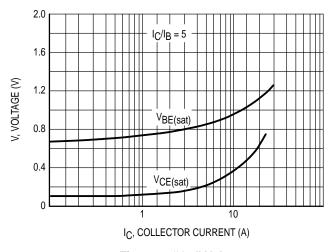


Figure 3. "On" Voltages

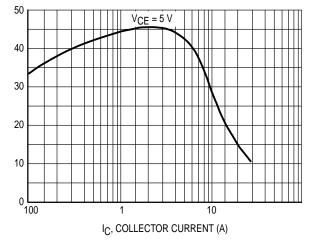


Figure 4. DC Current Gain

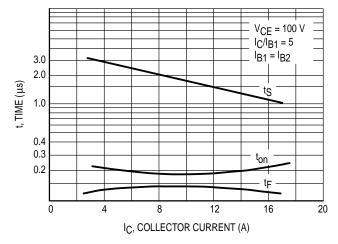
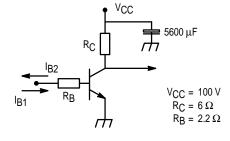


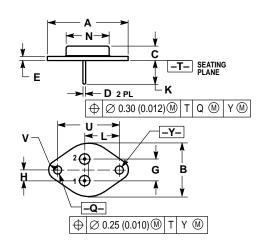
Figure 5. Resistive Switching Performance



R_C – R_B: Non inductive resistances

Figure 6. Switching Times Test Circuit

PACKAGE DIMENSIONS



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	1.530 REF		38.86 REF		
В	0.990	1.050	25.15	26.67	
С	0.250	0.335	6.35	8.51	
D	0.057	0.063	1.45	1.60	
Е	0.060	0.070	1.53	1.77	
G	0.430 BSC		10.92 BSC		
Н	0.215 BSC		5.46 BSC		
K	0.440	0.480	11.18	12.19	
L	0.665	BSC	16.89 BSC		
N	0.760	0.830	19.31	21.08	
Q	0.151	0.165	3.84	4.19	
U	1.187 BSC		30.15 BSC		
٧	0.131	0.188	3.33	4.77	

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

CASE 197A-05 TO-204AE (TO-3) **ISSUE J**

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